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# XPX4816XS

## **Dual N-Channel Enhancement Mode Power MOSFET**

#### • General Description

### • Pin Configurations





SOP-8L

# Package Marking and Ordering Information

| Device Marking | Device    | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| 4816           | XPX4816XS | SOP-8          | -         | -          | 3000     |

### • Absolute Maximum Ratings $@T_A=25^{\circ}C$ unless otherwise noted

| Para                                       | Symbol               | Ratings          | Unit    |    |
|--|----------------------|------------------|---------|----|
| Drain-Source Voltage                       | V <sub>DSS</sub>     | 30               | V       |    |
| Gate-Source Voltage                        | V <sub>GSS</sub>     | ±20              | V       |    |
| Drain Current (Continuous) *AC             | T <sub>A</sub> =25°C | - I <sub>D</sub> | 22      | ٨  |
|  | TA=70°C              |                  | 13      | A  |
| Drain Current (Pulse) *B                   |                      | I <sub>DM</sub>  | 44.8    | А  |
| Power Dissipation                          | T <sub>A</sub> =25°C | P <sub>D</sub>   | 3       | W  |
| Operating Temperature/ Storage Temperature |                      | TJ/TSTG          | -55~150 | °C |

### • Thermal Resistance Ratings

| Parameter                   | Symbol  | Typical           | Unit |      |
|-----------------------------|---------|-------------------|------|------|
| Maximum Junction-to-Ambient | t ≤ 10s | R <sub>thJA</sub> | 62.5 | °C/W |



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| Parameter                         | Symbol                | Test Conditions   | Min | Тур  | Max  | Unit |
|-----------------------------------|-----------------------|---|-----|------|------|------|
| Static                            |                       |   |     |      |      |      |
| Drain-Source Breakdown Voltage    | V <sub>(BR)DSS</sub>  | $V_{GS} = 0V, I_{D} = 250 \mu A$                            | 30  |      |      | V    |
| Zero Gate Voltage Drain Current   | I <sub>DSS</sub>      | $V_{DS} = 30V, V_{GS} = 0V$                                 |     |      | 1    | μA   |
| Gate Threshold Voltage            | V <sub>GS(TH)</sub>   | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>DS</sub> = 250µA | 1   | 1.7  | 2.5  | V    |
| Gate Leakage Current              | I <sub>GSS</sub>      | Vgs= ±20V, Vds=0V   |     |      | ±100 | nA   |
| Durin Courses On state Desistance | R <sub>DS(on)</sub>   | $V_{GS} = 10V, I_D = 12A$                                   |     | 7.5  | 10   | mΩ   |
| Drain-Source On-state Resistance  | R <sub>DS(on)</sub>   | $V_{GS} = 4.5V, I_D = 10A$                                  |     | 10.5 | 14   | mΩ   |
| Diode Forward Voltage             | V <sub>SD</sub>       | Isd= 1A , Vgs=0V  |     | 0.73 | 1.2  | V    |
| Diode Forward Current *AC         | ls                    | T <sub>A</sub> =25°C  |     |      | 2.7  | А    |
| Switching                         |                       |   |     |      |      | •    |
| Total Gate Charge                 | Qg                    |   |     | 14.7 |      | nC   |
| Gate-Source Charge                | Q <sub>gs</sub>       | Vgs=10V, Vds=15V, Id=9A                                     |     | 2.8  |      | nC   |
| Gate-Drain Charge                 | Q <sub>gd</sub>       |   |     | 1.8  |      | nC   |
| Turn-on Delay Time                | t <sub>d (on)</sub>   |   |     | 11   |      | ns   |
| Turn-on Rise Time                 | tr                    | Vgs=10V, Vds=15V, Id= 9A,                                   |     | 3.8  |      | ns   |
| Turn-off Delay Time               | t <sub>d( off )</sub> | $R_{GEN}=0.3\Omega$   |     | 31   |      | ns   |
| Turn-Off Fall Time                | tr                    |   |     | 6.5  |      | ns   |
| Dynamic                           |                       |   | -   | •    |      |      |
| Input Capacitance                 | Ciss                  |   |     | 950  |      | pF   |
| Output Capacitance                | Coss                  | Vgs=0V, Vds=15V, f=1MHz                                     |     | 162  |      | pF   |
| Reverse Transfer Capacitance      | Crss                  |   |     | 83   |      | pF   |

A: The value of R  $\oplus$  JA is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given

application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating





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Figure 5. Gate Threshold Variation with Temperature



Figure 2. Transfer Characteristics



Figure 4. On-Resistance Variation with Temperature



Figure 6. Body Diode Forward Voltage Variation with Source Current



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Figure 7. Gate Charge



Figure 9. Switching Test Circuit



Figure 8. Maximum Safe Operating Area



Figure 10. Switching Waveforms



Square Wave Pulse Duration (sec)

Figure 11. Normalized Thermal Transient Impedance Curve



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Package Information







### RECOMMENDED LAND PATTERN



| SYMBOLS   | DIMENSIONS IN MILLIMETERS |          |      | DIMENSIONS IN INCHES |       |       |
|-----------|---------------------------|----------|------|----------------------|-------|-------|
| 3 I MBOLS | MIN                       | NOM      | MAX  | MIN                  | NOM   | MAX   |
| Α         | 1.35                      | 1.65     | 1.75 | 0.053                | 0.065 | 0.069 |
| A1        | 0.10                      | 0.15     | 0.25 | 0.004                | 0.006 | 0.010 |
| A2        | 1.25                      | 1.50     | 1.65 | 0.049                | 0.059 | 0.065 |
| b         | 0.31                      | 0.41     | 0.51 | 0.012                | 0.016 | 0.020 |
| с         | 0.17                      | 0.20     | 0.25 | 0.007                | 0.008 | 0.010 |
| D         | 4.80                      | 4.90     | 5.00 | 0.189                | 0.193 | 0.197 |
| E         | 3.80                      | 3.90     | 4.00 | 0.150                | 0.154 | 0.157 |
| е         | 1                         | 1.27 BSC |      | 0.050 BSC            |       |       |
| E1        | 5.80                      | 6.00     | 6.20 | 0.228                | 0.236 | 0.244 |
| h         | 0.25                      | 0.30     | 0.50 | 0.010                | 0.012 | 0.020 |
| L         | 0.40                      | 0.69     | 1.27 | 0.016                | 0.027 | 0.050 |
| θ         | 0°                        | 4°       | 8°   | 0°                   | 4°    | 8°    |

NOTE

1. ALL DIMENSIONS ARE IN MILLMETERS.

2. DIMENSIONS ARE INCLUSIVE OF PLATING.

3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.

MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.

4. DIMENSION L IS MEASURED IN GAUGE PLANE.

5. CONTROLLING DIMENSION IS MILLIMETER.

CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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#### Flow (wave) soldering (solder dipping)

| Product        | Peak Temperature            | Dipping Time |  |  |
|----------------|-----------------------------|--------------|--|--|
| Pb device      | <b>245℃±5</b> ℃             | 5sec±1sec    |  |  |
| Pb-Free device | <b>260</b> ℃ <b>+0/-5</b> ℃ | 5sec±1sec    |  |  |



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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